

isc Silicon NPN RF Transistor

2SC4264

DESCRIPTION

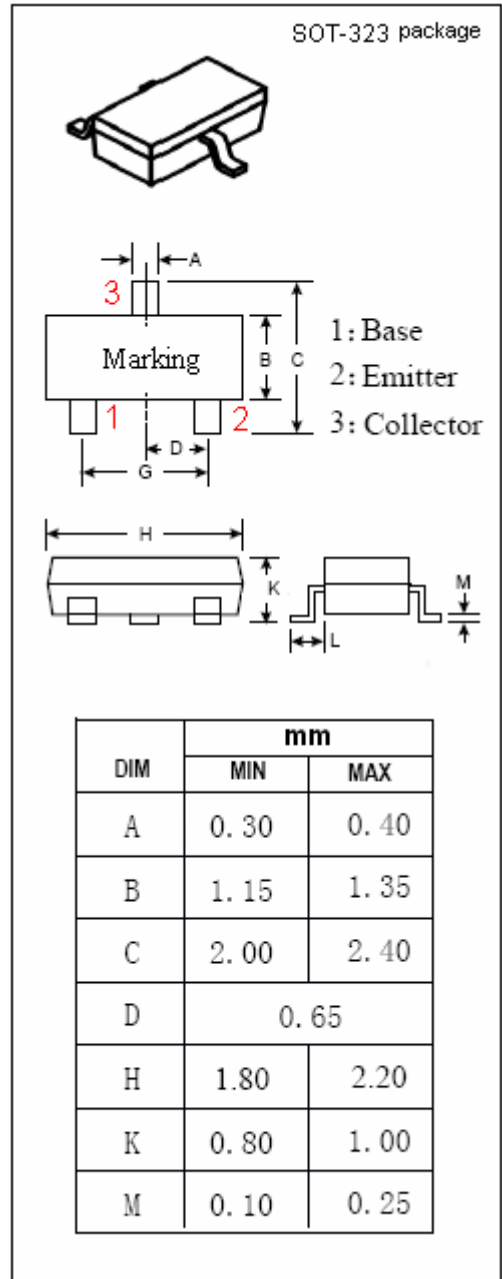
- Low Noise
- High Gain

APPLICATIONS

- Designed for use in UHF ~VHF RF amplifier, local oscillator, mixer.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	11	V
V _{EBO}	Emitter-Base Voltage	3.0	V
I _C	Collector Current-Continuous	50	mA
P _C	Collector Power Dissipation @T _C =25°C	0.1	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



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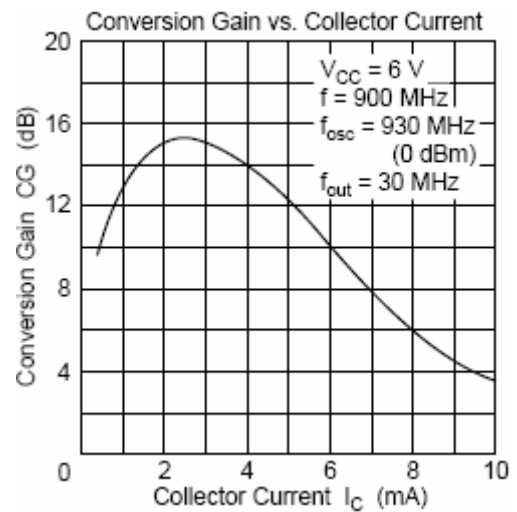
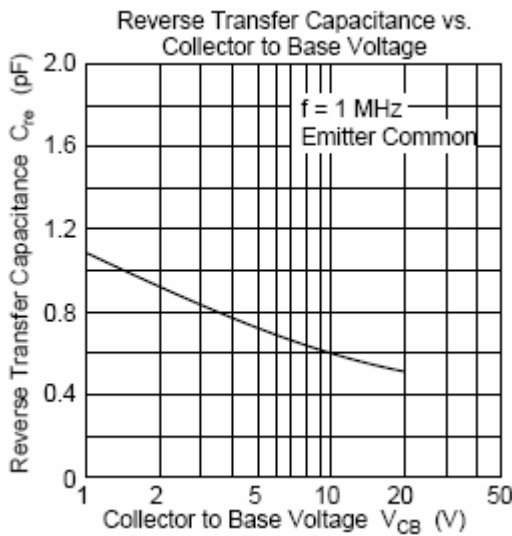
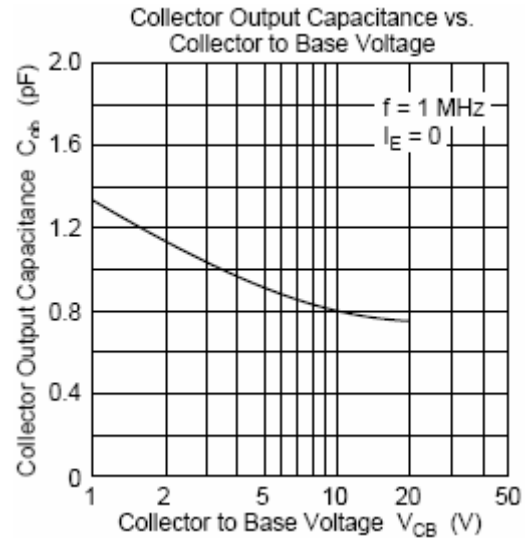
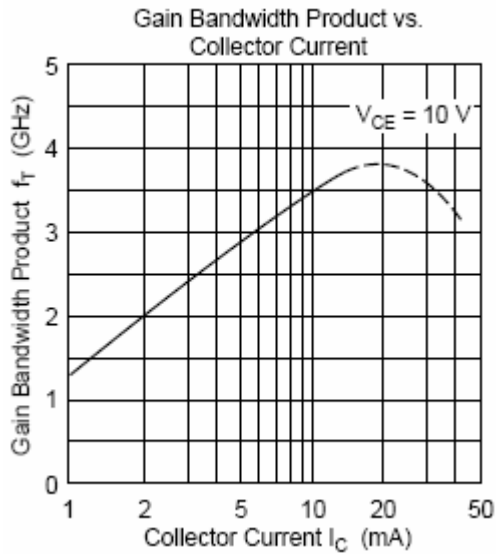
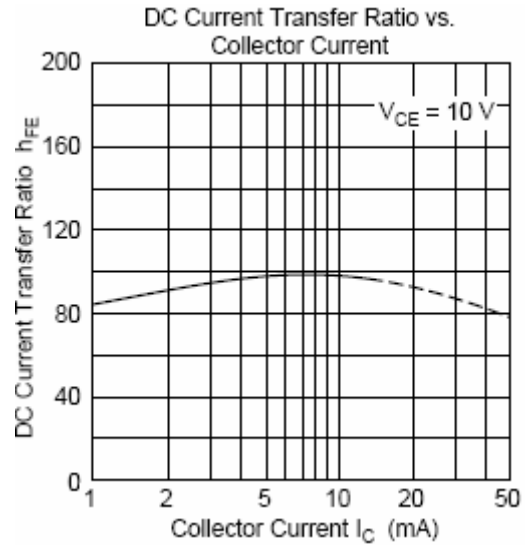
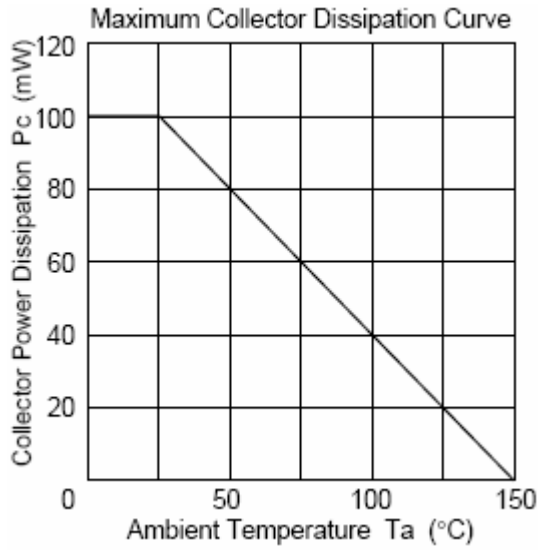
ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 10 μ A ; I _E = 0	20			V
I _{CBO}	Collector Cutoff Current	V _{CB} = 15V; I _E = 0			0.5	μ A
I _{CEO}	Collector Cutoff Current	V _{CE} = 11V; R _{BE} = ∞			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 3V; I _C = 0			1.0	μ A
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10mA ; I _B = 5mA			0.7	V
h _{FE}	DC Current Gain	I _C = 5mA ; V _{CE} = 10V	20			
f _T	Current-Gain—Bandwidth Product	I _C = 10mA ; V _{CE} = 10V	1.4			GHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V;f= 1.0MHz			1.5	pF

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